2302W

N-Channel Trench Power MOSFET

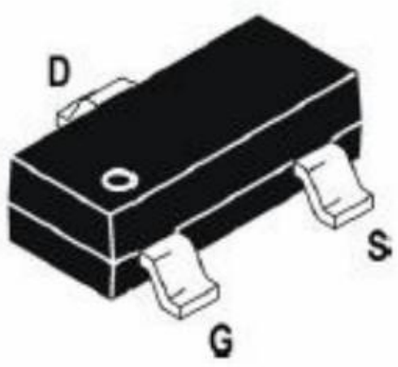
Features

- VDS=20V, ID=3.2A
- RDS(ON) <68 mΩ @ VGS = 2.5V
- RDS(ON <59mΩ @ VGS = 4.5V
- High Power and Current Handing Capability
- Trench Power LV MOSFET technology

Application

- PWM Applications
- Load Switch

Package



SOT-23



Absolute Maximum Ratings (Tc=25℃ unless otherwise specified)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		VDS	20	V
Gate-source Voltage		VGS	±12	V
Drain Current	TA=25℃ @ Steady State	ID	3.2	A
	TA=70℃ @ Steady State		2.1	
Pulsed Drain Current A		IDM	12.8	A
Total Power Dissipation @ TA=25℃		PD	1.18	W
Thermal Resistance Junction-to-Ambient @ Steady State B		RθJA	120	℃/W
Junction and Storage Temperature Range		TJ ,TSTG	-55～+150	℃

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